

Electron Confinement in Graphene Nanoislands with Free-electron-like Energy Dispersion

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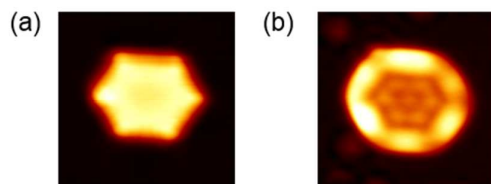


Figure. S1. (a) STM image of a GN with hexagonal shape ($V_s = 0.1$ V, $I_t = 1.0$ nA, Scan area: 5.5×5.5 nm²). (b) dI/dV map measured at the sample bias voltage of 3.9 V.

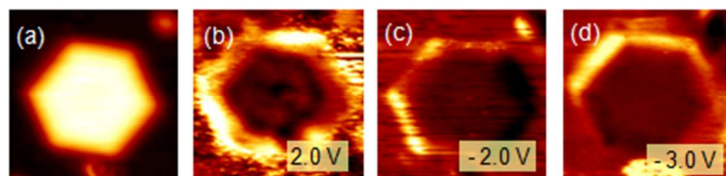


Figure. S2. (a) STM image of the GN ($V_s = -2.0$ V, $I_t = 1.0$ nA, Scan area: 4.5×4.5 nm²). (b) – (d) dI/dV maps.

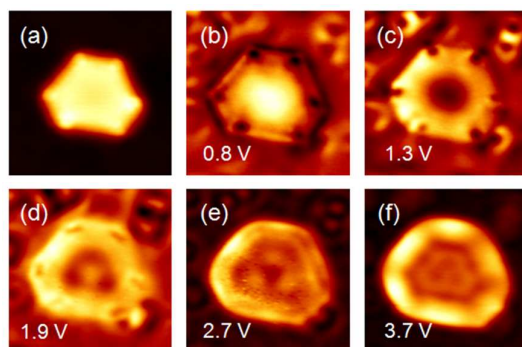


Figure. S3. (a) STM image of the GN ($V_s = 0.01$ V, $I_t = 7.0$ nA, Scan area: 5×5 nm²). (b) – (f) dI/dV maps.